

T-33-19

## SILICON POWER TRANSISTORS

P-N-P epitaxial-base power transistors in the plastic SOT-93 envelope. These transistors are intended for use in audio output stages and general amplifier and switching applications. N-P-N complements are TIP33, TIP33A, TIP33B and TIP33C.

## QUICK REFERENCE DATA

			TIP34	34A	34B	34C	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80	100	120	140	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	60	80	100	V
Collector current (d.c.)	$-I_C$	max.			10		A
Collector current (peak value); $t_p \leq 0,3$ ms	$-I_{CM}$	max.			15		A
Power dissipation up to $T_{mb} = 25$ °C	$P_{tot}$	max.			80		W
D.C. current gain $-V_{CE} = 4$ V; $-I_C = 3$ A	$h_{FE}$				20 to 100		
Collector-emitter saturation voltage $-I_C = 3$ A; $-I_B = 0,3$ A	$-V_{CESat}$	<		1			V

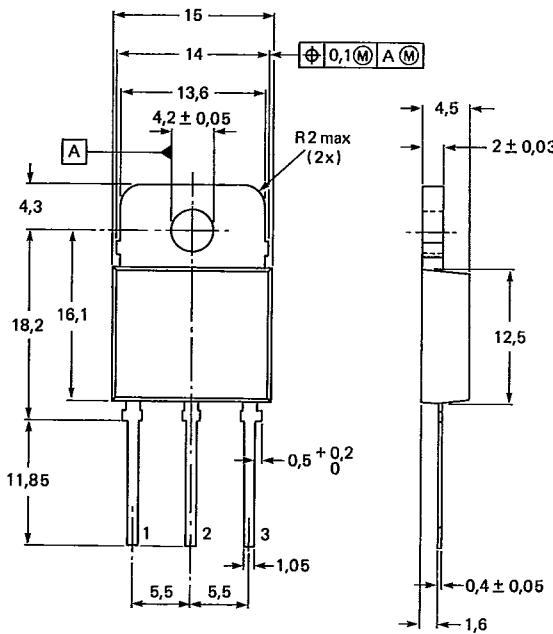
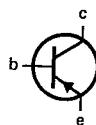
## MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-93.

Collector connected  
to mounting base.

Pinning:  
1 = base  
2 = collector  
3 = emitter



7296696

## RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

		TIP34	34A	34B	34C	V
Collector-base voltage (open emitter)	-V <sub>CBO</sub>	max.	80	100	120	140
Collector-emitter voltage (open base)	-V <sub>CEO</sub>	max.	40	60	80	100
Emitter-base voltage (open collector)	-V <sub>EBO</sub>	max.	5	5	5	5
Collector current (d.c.)	-I <sub>C</sub>	max.			10	A
Collector current (peak value); t <sub>p</sub> ≤ 0,3 ms	-I <sub>CM</sub>	max.			15	A
Base current (d.c.)	-I <sub>B</sub>	max.			3	A
Total power dissipation up to T <sub>mb</sub> = 25 °C	P <sub>tot</sub>	max.			80	W
Total power dissipation in free air	P <sub>tot</sub>	max.			3,5	W
Storage temperature	T <sub>stg</sub>				-65 to + 150	°C
Junction temperature	T <sub>j</sub>	max.			150	°C

## THERMAL RESISTANCE

From junction to mounting base	R <sub>th j-mb</sub>	=	1,56	K/W
From junction to ambient in free air	R <sub>th j-a</sub>	=	35,7	K/W

## CHARACTERISTICS

T<sub>j</sub> = 25 °C unless otherwise specified

## Collector cut-off currents

-V <sub>CE</sub> = -V <sub>CBOmax</sub> ; V <sub>BE</sub> = 0	-I <sub>CES</sub>	<	0,4	mA	
-V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	TIP34	-I <sub>CEO</sub>	<	0,2	mA
	TIP34A	-I <sub>CEO</sub>	<	0,2	mA
-V <sub>CE</sub> = 60 V; I <sub>B</sub> = 0	TIP34B	-I <sub>CEO</sub>	<	0,2	mA
	TIP34C	-I <sub>CEO</sub>	<	0,2	mA

## Emitter cut-off current

-V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	-I <sub>EBO</sub>	<	0,1	mA
--------------------------------------------	-------------------	---	-----	----

## Collector-emitter sustaining voltage

-I <sub>C</sub> = 30 mA; I <sub>B</sub> = 0	TIP34	-V <sub>CEO</sub> sust	>	40	V
	TIP34A	-V <sub>CEO</sub> sust	>	60	V
	TIP34B	-V <sub>CEO</sub> sust	>	80	V
	TIP34C	-V <sub>CEO</sub> sust	>	100	V

## D.C. current gain

-V <sub>CE</sub> = 4 V; -I <sub>C</sub> = 1 A	h <sub>FE</sub>	>	40	
-V <sub>CE</sub> = 4 V; -I <sub>C</sub> = 3 A	h <sub>FE</sub>		20 to 100	

## Base-emitter voltage

-V <sub>CE</sub> = 4 V; -I <sub>C</sub> = 3 A	-V <sub>BE</sub>	<	1,6	V
-V <sub>CE</sub> = 4 V; -I <sub>C</sub> = 10 A	-V <sub>BE</sub>	<	3	V

PHILIPS INTERNATIONAL

56E D

■ 7110826 0043514 293 ■ PHIN

## Collector-emitter saturation voltage

 $-I_C = 3 \text{ A}; -I_B = 0,3 \text{ A}$  $-V_{CEsat} < 1 \text{ V}$  $-I_C = 10 \text{ A}; -I_B = 2,5 \text{ A}$  $-V_{CEsat} < 4 \text{ V}$ 

## Small-signal current gain

 $-V_{CE} = 10 \text{ V}; -I_C = 0,5 \text{ A}; f = 1 \text{ kHz}$  $h_{fe} > 20$ 

## Transition frequency

 $-V_{CE} = 10 \text{ V}; -I_C = 0,5 \text{ A}; f = 1 \text{ MHz}$  $f_T > 3 \text{ MHz}$ 

## Turn-off breakdown energy (see Fig. 2)

 $L = 20 \text{ mH}; -I_C = 2,5 \text{ A}$  $E_{(BR)} > 62,5 \text{ mJ}$ 

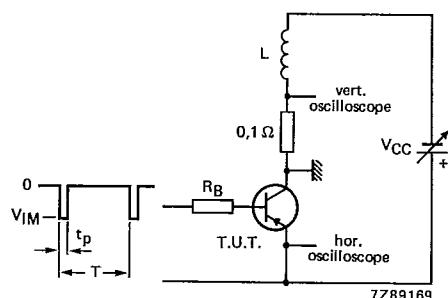
## Switching times (see Figs 3 and 4)

 $-I_C = 6 \text{ A}; -I_{Bon} = +I_{Boff} = 0,6 \text{ A}; -V_{CC} = 30 \text{ V}$  $t_{on} \text{ typ. } 0,4 \mu\text{s}$ 

turn-on time

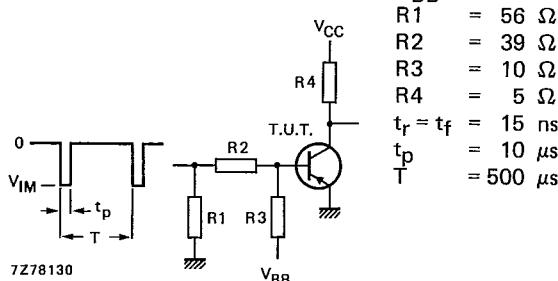
 $t_{off} \text{ typ. } 0,7 \mu\text{s}$ 

turn-off time



$-V_{IM} = 12 \text{ V}$   
 $R_B = 270 \Omega$   
 $L = 20 \text{ mH}$   
 $-I_{CC} = 2,5 \text{ A}$   
 $t_p = 1 \text{ ms}$   
 $\delta = 1 \%$

Fig. 2 Test circuit for turn-off breakdown energy.



$-V_{IM} = 47 \text{ V}$   
 $-V_{CC} = 30 \text{ V}$   
 $V_{BB} = 4 \text{ V}$   
 $R_1 = 56 \Omega$   
 $R_2 = 39 \Omega$   
 $R_3 = 10 \Omega$   
 $R_4 = 5 \Omega$   
 $t_r = t_f = 15 \text{ ns}$   
 $t_p = 10 \mu\text{s}$   
 $T = 500 \mu\text{s}$

Fig. 3 Switching times test circuit.

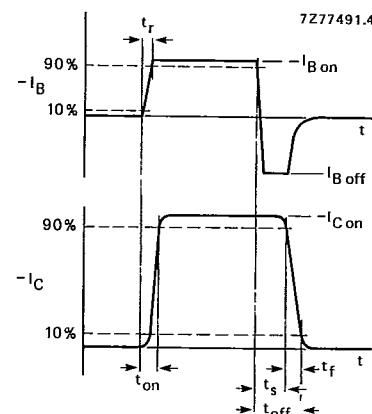
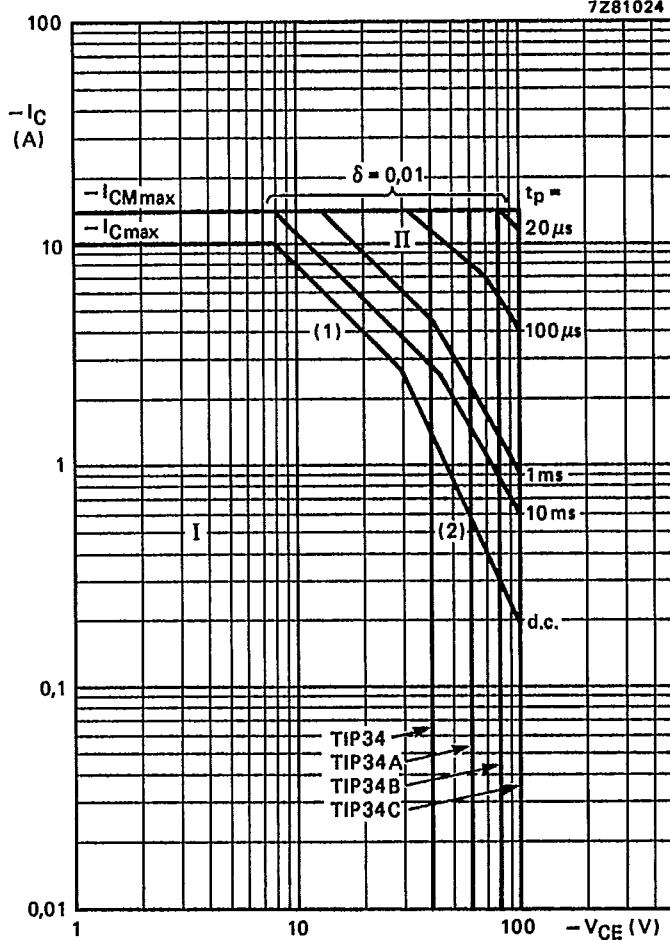


Fig. 4 Switching times waveforms.

7281024



T-33-19

Fig. 5 Safe Operating Area at  $T_{mb} = 25\text{ }^{\circ}\text{C}$ .

I Region of permissible d.c. operation.

II Permissible extension for repetitive pulse operation.

(1)  $P_{tot\ max}$  and  $P_{tot\ peak\ max}$  lines.

(2) Second breakdown limits.

PHILIPS INTERNATIONAL

56E D ■ 7110826 0043516 066 ■ PHIN

T-33-19

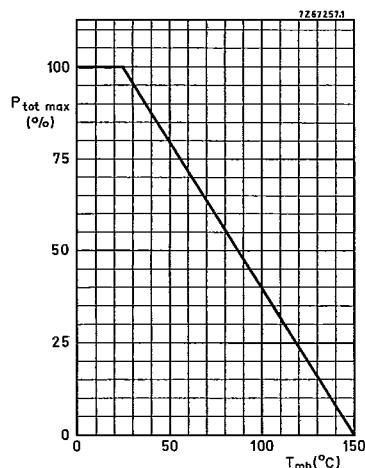
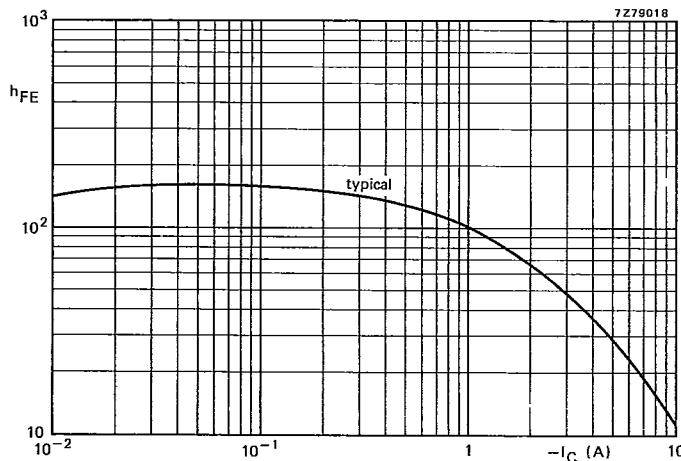
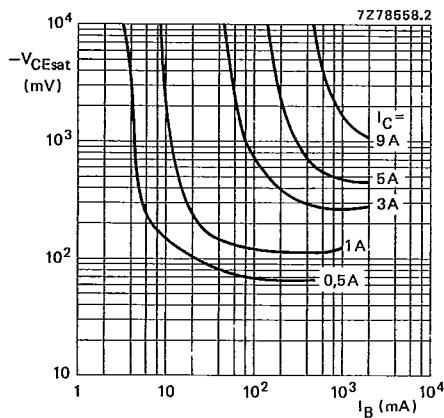


Fig. 6 Power derating curve.

Fig. 7  $-V_{CE} = 4$  V;  $T_j = 25$  °C.Fig. 8 Typical collector-emitter saturation voltage.  $T_j = 25$  °C.